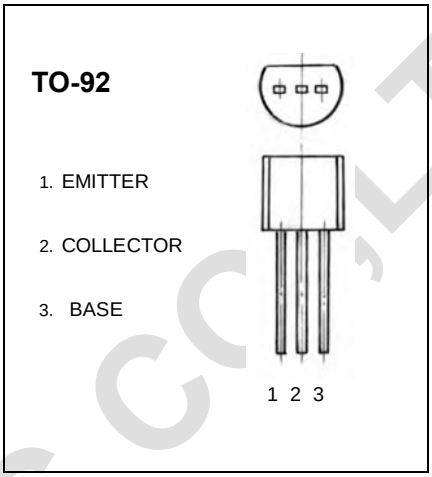
BC640 TRANSISTOR (PNP)



FEATURES

Power dissipation

$P_{CM:}$ 0.83 W (Tamb=25℃)

Collector current

$I_{CM:}$ - 1 A

Collector-base voltage

$V_{(BR)CBO}$: -100 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -100μA, I_E=0	-100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=- 1mA, I_B=0	- 80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-30V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V, I_C=0			- 0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -2V, I_C=- 5mA	40			
	$h_{FE(2)}$	V_{CE}= -2V, I_C=- 150mA	63		250	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=- 500mA, I_B= -50mA			-0.5	V
Base-emitter voltage	V_{BE}	V_{CE}= -2V, I_C= -500mA			- 1	V
Transition frequency	f_T	V_{CE}= -5V, I_C=- 50mA,		100		MHz

CLASSIFICATION OF $h_{FE(2)}$

Rank	A	B
Range	63-160	100-250